

Saeed Jahdi

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of Carriers Injection Level on Transients of Discrete and Paralleled Silicon and 4H-SiC NPN BJTs. IEEE Open Journal of the Industrial Electronics Society, 2022, 3, 65-80.	4.8	1
2	Crosstalk Induced Shoot-Through in BTI-Stressed Symmetrical & Asymmetrical Double-Trench SiC Power MOSFETs. IEEE Open Journal of the Industrial Electronics Society, 2022, 3, 188-202.	4.8	5
3	Analysis of the 1st and 3rd Quadrant Transients of Symmetrical and Asymmetrical Double-Trench SiC Power MOSFETs. IEEE Open Journal of Power Electronics, 2021, 2, 265-276.	4.0	7
4	Prospects and Challenges of 4H-SiC Thyristors in Protection of HB-MMC-VSC-HVDC Converters. IEEE Open Journal of Power Electronics, 2021, 2, 145-154.	4.0	5
5	Performance of wide-bandgap discrete and module cascodes at sub-1kV: GaN vs. SiC. Microelectronics Reliability, 2021, 125, 114362.	0.9	2
6	Impact of Temperature and Switching Rate on Forward and Reverse Conduction of GaN and SiC Cascode devices: A Technology Evaluation. , 2021, , .		0
7	Measurement and simulation of short circuit current sharing under parallel connection: SiC MOSFETs and SiC Cascode JFETs. Microelectronics Reliability, 2021, 126, 114271.	0.9	7
8	Performance of Parallel Connected SiC MOSFETs under Short Circuits Conditions. Energies, 2021, 14, 6834.	1.6	12
9	Impact of Temperature and Switching Rate on Properties of Crosstalk on Symmetrical & Asymmetrical Double-trench SiC Power MOSFET. , 2021, , .		4
10	Comparison of Short Circuit Failure Modes in SiC Planar MOSFETs, SiC Trench MOSFETs and SiC Cascode JFETs. , 2021, , .		12
11	Current Sharing of Parallel SiC MOSFETs under Short Circuit Conditions. , 2021, , .		11
12	The Impact of Temperature and Switching Rate on Dynamic Transients of High-Voltage Silicon and 4H-SiC NPN BJTs: A Technology Evaluation. IEEE Transactions on Industrial Electronics, 2020, 67, 4556-4566.	5.2	4
13	Performance and Reliability Review of 650 V and 900 V Silicon and SiC Devices: MOSFETs, Cascode JFETs and IGBTs. IEEE Transactions on Industrial Electronics, 2020, 67, 7375-7385.	5.2	106
14	Analysis of cyclic spontaneous switchings in GaN & SiC cascodes by snappy turn-off currents. Microelectronics Reliability, 2020, 114, 113752.	0.9	2
15	UIS performance and ruggedness of stand-alone and cascode SiC JFETs. Microelectronics Reliability, 2020, 114, 113803.	0.9	7
16	Performance of Wide-Bandgap Gallium Nitride vs Silicon Carbide Cascode Transistors. , 2020, , .		2
17	Dynamic characterization of SiC and GaN devices with BTI stresses. Microelectronics Reliability, 2019, 100-101, 113389.	0.9	7
18	Temperature and Switching Rate Dependence of Crosstalk in Si-IGBT and SiC Power Modules. IEEE Transactions on Industrial Electronics, 2016, 63, 849-863.	5.2	114

#	ARTICLE	IF	CITATIONS
19	Physics-based modelling and experimental characterisation of parasitic turn-on in IGBTs. , 2015, , .		6
20	Modeling of temperature dependent parasitic gate turn-on in silicon IGBTs. , 2015, , .		1
21	Analysis of power device failure under avalanche mode Conduction. , 2015, , .		8
22	The Impact of Temperature and Switching Rate on the Dynamic Characteristics of Silicon Carbide Schottky Barrier Diodes and MOSFETs. IEEE Transactions on Industrial Electronics, 2015, 62, 163-171.	5.2	53
23	Analytical Modeling of Switching Energy of Silicon Carbide Schottky Diodes as Functions of $\frac{dI}{dt}$ and Temperature. IEEE Transactions on Power Electronics, 2015, 30, 3345-3355.	5.4	13
24	An Analysis of the Switching Performance and Robustness of Power MOSFETs Body Diodes: A Technology Evaluation. IEEE Transactions on Power Electronics, 2015, 30, 2383-2394.	5.4	65
25	Compact Electrothermal Reliability Modeling and Experimental Characterization of Bipolar Latchup in SiC and CoolMOS Power MOSFETs. IEEE Transactions on Power Electronics, 2015, 30, 6978-6992.	5.4	29
26	Accurate Analytical Modeling for Switching Energy of PiN Diodes Reverse Recovery. IEEE Transactions on Industrial Electronics, 2015, 62, 1461-1470.	5.2	34
27	Comparative analysis of false turn-ON in silicon bipolar and SiC unipolar power devices. , 2015, , .		13
28	Investigation of parasitic turn-ON in silicon IGBT and Silicon Carbide MOSFET devices: A technology evaluation. , 2015, , .		8
29	Electrothermal modeling and characterization of SiC Schottky and silicon PiN diodes switching transients. , 2014, , .		1
30	Modeling of turn-OFF transient energy in IGBT controlled silicon PiN diodes. , 2014, , .		1
31	Investigating the reliability of SiC MOSFET body diodes using Fourier series modelling. , 2014, , .		14
32	An Evaluation of Silicon Carbide Unipolar Technologies for Electric Vehicle Drive-Trains. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2014, 2, 517-528.	3.7	59
33	Improved Electrothermal Ruggedness in SiC MOSFETs Compared With Silicon IGBTs. IEEE Transactions on Electron Devices, 2014, 61, 2278-2286.	1.6	56
34	The impact of silicon carbide technology on grid-connected Distributed Energy resources. , 2013, , .		3
35	Renewable Hybrids Grid-Connection Using Converter Interferences. International Journal of Sustainable Energy Development, 2013, 2, 56-62.	0.4	4
36	Energy saving in drives using ZCT ZVT DC-DC converters, PWM inverters in variable speed compressor applications. , 2011, , 283-294.		1

#	ARTICLE	IF	CITATIONS
37	Voltage profile stability analysis of radial distribution power systems in presence of DGs. , 2011, , .		3
38	DC-DC converters application in fuel-cell stack grid integration. , 2011, , .		1
39	DG modeling and compensation methods in distribution load flow analysis and voltage profile recovery. , 2011, , .		4
40	DG islanding operation detection methods in combination of harmonics protection schemes. , 2011, , .		3
41	Affects of TCSC usages on Distance protection and Voltage profile of a system; a novel. , 2011, , .		2
42	Grid integration of wind-solar hybrid renewables using AC/DC converters as DG power sources. , 2011, , .		11
43	Temperature and $\frac{dI}{dt}$ Dependence of the Switching Energy of SiC Schottky Diodes in Clamped Inductive Switching Applications. Materials Science Forum, 0, 778-780, 816-819.	0.3	0
44	Cryogenic Characterization of Commercial SiC Power MOSFETs. Materials Science Forum, 0, 821-823, 777-780.	0.3	13